















The 4N35, 4N36 and 4N37 devices consist of a gallium arsenide infrared emitting diode optically coupled to a monolithic silicon phototransistor detector.

- Current Transfer Ratio 100% Minimum @ Specified Conditions
- · Guaranteed Switching Speeds
- Meets or Exceeds all JEDEC Registered Specifications
- To order devices that are tested and marked per VDE 0884 requirements, the suffix "V" must be included at end of part number. VDE 0884 is a test option.

#### **Applications**

- General Purpose Switching Circuits
- Interfacing and coupling systems of different potentials and impedances
- · Regulation Feedback Circuits
- · Monitor & Detection Circuits
- Solid State Relays

# **MAXIMUM RATINGS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Rating	Symbol	Value	Unit	
INPUT LED				
Reverse Voltage	٧R	6	Volts	
Forward Current — Continuous	lF	60	mA	
LED Power Dissipation @ T <sub>A</sub> = 25°C with Negligible Power in Output Detector	PD	120	mW	
Derate above 25°C		1.41	mW/°C	
OUTPUT TRANSISTOR				

Collector–Emitter Voltage	V <sub>CEO</sub>	30	Volts
Emitter–Base Voltage		7	Volts
Collector–Base Voltage	VCBO	70	Volts
Collector Current — Continuous	IC	150	mA
Detector Power Dissipation @ T <sub>A</sub> = 25°C with Negligible Power in Input LED Derate above 25°C	PD	150 1.76	mW mW/°C

#### **TOTAL DEVICE**

Isolation Source Voltage <sup>(1)</sup> (Peak ac Voltage, 60 Hz, 1 sec Duration)	VISO	7500	Vac(pk)
Total Device Power Dissipation @ T <sub>A</sub> = 25°C Derate above 25°C		250 2.94	mW mW/°C
Ambient Operating Temperature Range <sup>(2)</sup>		-55 to +100	°C
Storage Temperature Range(2)		-55 to +150	°C
Soldering Temperature (10 sec, 1/16" from case)	TL	260	°C

- 1. Isolation surge voltage is an internal device dielectric breakdown rating. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.
- 2. Refer to Quality and Reliability Section in Opto Data Book for information on test conditions.

Preferred devices are Motorola recommended choices for future use and best overall value.

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# 4N35\*

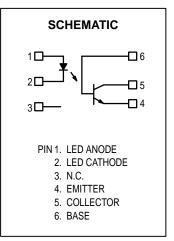
**4N36** 

**4N37** 

[CTR = 100% Min]

\*Motorola Preferred Device







## 4N35 4N36 4N37

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$  unless otherwise noted)(1)

Forward Voltage (IF = 10 mA)  Forward Voltage (IF = 10 mA)  TA = 25°C TA = 55°C TA = 100°C  Reverse Leakage Current (VR = 6 V)  Capacitance (V = 0 V, f = 1 MHz)  CUITPUT TRANSISTOR  Collector–Emitter Dark Current (VCE = 10 V, TA = 25°C) (VCE = 30 V, TA = 100°C)  Collector–Base Dark Current (VCB = 10 V)  TA = 25°C TA = 100°C  Collector–Emitter Breakdown Voltage (IC = 1 mA)  Collector–Base Breakdown Voltage (IC = 100 $\mu$ A)  Emitter–Base Breakdown Voltage (IE = 100 $\mu$ A)  DC Current Gain (IC = 2 mA, VCE = 5 V)  Collector–Emitter Capacitance (f = 1 MHz, VCB = 0)  Emitter–Base Capacitance (f = 1 MHz, VCB = 0)  CCB  COUPLED  Output Collector Current (IF = 10 mA, VCE = 10 V)  TA = 25°C TA = 55°C TA = 100°C  CEB  COUPLED  Output Collector Current (IF = 10 mA, VCE = 10 V)  TA = 25°C TA = 100°C  COllector–Emitter Saturation Voltage (IC = 0.5 mA, IF = 10 mA)  VCE(sat)  Turn–On Time  Turn–On Time  Turn–Off Time  Rise Time  Fall Time	0.8 0.9 0.7 — — — — — — — — 30 70	1.15 1.3 1.05 — 18  1 — 0.2 100 45 100	1.5 1.7 1.4 10 — 50 500 20	V μA pF nA μA
Reverse Leakage Current ( $V_R = 6 \text{ V}$ )  Reverse Leakage Current ( $V_R = 6 \text{ V}$ )  Capacitance ( $V_R = 6 \text{ V}$ )  Capacitance ( $V_R = 6 \text{ V}$ )  Collector-Emitter Dark Current ( $V_R = 6 \text{ V}$ )  Collector-Emitter Dark Current ( $V_R = 6 \text{ V}$ )  Collector-Emitter Dark Current ( $V_R = 6 \text{ V}$ )  Collector-Base Dark Current ( $V_R = 6 \text{ V}$ )  Collector-Base Dark Current ( $V_R = 6 \text{ V}$ )  Collector-Base Dark Current ( $V_R = 6 \text{ V}$ )  Collector-Base Dark Current ( $V_R = 6 \text{ V}$ )  Collector-Base Dark Current ( $V_R = 6 \text{ V}$ )  Collector-Emitter Breakdown Voltage ( $V_R = 6 \text{ V}$ )  Collector-Emitter Breakdown Voltage ( $V_R = 6 \text{ V}$ )  Collector-Base Breakdown Voltage ( $V_R = 6 \text{ V}$ )  Collector-Base Breakdown Voltage ( $V_R = 6 \text{ V}$ )  Collector-Emitter Capacitance ( $V_R = 6 \text{ V}$ )  Collector-Emitter Capacitance ( $V_R = 6 \text{ V}$ )  Collector-Emitter Capacitance ( $V_R = 6 \text{ V}$ )  Collector-Base Capacitance ( $V_R = 6 \text{ V}$ )  C	0.9 0.7 ———————————————————————————————————	1.3 1.05 — 18 1 — 0.2 100 45	1.7 1.4 10 — 50 500 20	μA pF nA μA
Capacitance (V = 0 V, f = 1 MHz)  CJ  DUTPUT TRANSISTOR  Collector–Emitter Dark Current (V <sub>CE</sub> = 10 V, T <sub>A</sub> = 25°C) (V <sub>CE</sub> = 30 V, T <sub>A</sub> = 100°C)  Collector–Base Dark Current (V <sub>CB</sub> = 10 V)  Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 1 mA)  Collector–Base Breakdown Voltage (I <sub>C</sub> = 1 mA)  Collector–Base Breakdown Voltage (I <sub>C</sub> = 100 $\mu$ A)  Emitter–Base Breakdown Voltage (I <sub>E</sub> = 100 $\mu$ A)  Collector–Emitter Capacitance (f = 1 MHz, V <sub>CB</sub> = 0)  Collector–Emitter Capacitance (f = 1 MHz, V <sub>CB</sub> = 0)  Collector–Base Capacitance (f = 1 MHz, V <sub>CB</sub> = 0)  CoupleD  Output Collector Current (I <sub>F</sub> = 10 mA, V <sub>CE</sub> = 10 V)  Collector–Emitter Saturation Voltage (I <sub>C</sub> = 0.5 mA, I <sub>F</sub> = 10 mA)  Turn–On Time  Turn–On Time  (I <sub>C</sub> = 2 mA, V <sub>CC</sub> = 10 V, R <sub>L</sub> = 100 V, R <sub>L</sub> = 100 Ω)  (I <sub>C</sub> = 2 mA, V <sub>CC</sub> = 10 V, R <sub>L</sub> = 100 Q)  (I <sub>C</sub> = 2 mA, V <sub>CC</sub> = 10 V, R <sub>L</sub> = 100 Q)		18 1 — 0.2 100 45	50 500 20	pF nA μA
Collector–Emitter Dark Current ( $V_{CE} = 10 \text{ V}$ , $T_A = 25^{\circ}\text{C}$ ) ( $V_{CE} = 30 \text{ V}$ , $T_A = 100^{\circ}\text{C}$ )  Collector–Base Dark Current ( $V_{CB} = 10 \text{ V}$ )  Collector–Emitter Breakdown Voltage ( $I_{C} = 1 \text{ mA}$ )  Collector–Emitter Breakdown Voltage ( $I_{C} = 1 \text{ mA}$ )  Collector–Base Breakdown Voltage ( $I_{C} = 100 \text{ \mu A}$ )  Emitter–Base Breakdown Voltage ( $I_{C} = 100 \text{ \mu A}$ )  DC Current Gain ( $I_{C} = 2 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ )  Collector–Emitter Capacitance ( $I_{C} = 100 \text{ mA}$ )  Collector–Emitter Capacitance ( $I_{C} = 100 \text{ mA}$ )  Collector–Base Capacitance ( $I_{C} = 100 \text{ mA}$ )  Collector–Base Capacitance ( $I_{C} = 100 \text{ mA}$ )  Collector–Base Capacitance ( $I_{C} = 100 \text{ mA}$ )  Collector–Base Capacitance ( $I_{C} = 100 \text{ mA}$ )  Collector–Emitter Saturation Voltage ( $I_{C} = 0.5 \text{ mA}$ , $I_{C} = 10 \text{ mA}$ )  Collector–Emitter Saturation Voltage ( $I_{C} = 0.5 \text{ mA}$ , $I_{C} = 10 \text{ mA}$ )  Turn–On Time  Turn–On Time  ( $I_{C} = 2 \text{ mA}$ , $V_{CC} = 10 \text{ V}$ , $I_{C} = 100 \text{ mA}$ )  Collector–Emitter Saturation Voltage ( $I_{C} = 0.5 \text{ mA}$ , $I_{C} = 10 \text{ V}$ , $I_{C} = 100 \text{ mA}$ )  Collector–Emitter Saturation Voltage ( $I_{C} = 0.5 \text{ mA}$ , $I_{C} = 10 \text{ V}$ , $I_{C} = 100 \text{ MA}$ )  Collector–Emitter Saturation Voltage ( $I_{C} = 0.5 \text{ mA}$ , $I_{C} = 10 \text{ V}$ , $I_{C} = 100 \text{ MA}$ )  Collector–Emitter Saturation Voltage ( $I_{C} = 0.5 \text{ mA}$ , $I_{C} = 10 \text{ V}$ , $I_{C} = 100 \text{ MA}$ )	30 70	1 — 0.2 100 45	500 20	nA μA
Collector–Emitter Dark Current ( $V_{CE} = 10 \text{ V}$ , $T_A = 25^{\circ}\text{C}$ ) ( $V_{CE} = 30 \text{ V}$ , $T_A = 100^{\circ}\text{C}$ )  Collector–Base Dark Current ( $V_{CB} = 10 \text{ V}$ ) $V_{CE} = 30 \text{ V}$ , $V_{CE} = 100^{\circ}\text{C}$ Collector–Emitter Breakdown Voltage ( $V_{CE} = 100 \text{ J}$ )  Collector–Base Breakdown Voltage ( $V_{CE} = 100 \text{ J}$ )  Emitter–Base Breakdown Voltage ( $V_{CE} = 100 \text{ J}$ )  DC Current Gain ( $V_{CE} = 100 \text{ J}$ )  Collector–Emitter Capacitance ( $V_{CE} = 100 \text{ J}$ )  Collector–Emitter Capacitance ( $V_{CE} = 100 \text{ J}$ )  Collector–Base Capacitance ( $V_{CE} = 100 \text{ J}$ )  Collector–Base Capacitance ( $V_{CE} = 100 \text{ J}$ )  Collector–Base Capacitance ( $V_{CE} = 10 \text{ J}$ )  Couput Collector Current ( $V_{CE} = 10 \text{ J}$ )  Couput Collector Current ( $V_{CE} = 10 \text{ J}$ )  Collector–Emitter Saturation Voltage ( $V_{CE} = 10 \text{ J}$ )  Collector–Emitter Saturation Voltage ( $V_{CE} = 10 \text{ J}$ )  Turn–On Time ( $V_{CE} = 10 \text{ J}$ )  Turn–Off Time ( $V_{CE} = 10 \text{ J}$ )  Rise Time ( $V_{CE} = 10 \text{ J}$ )  Tapical Solve ( $V_{CE} = 10 \text{ J}$ )  Toro-Off Time ( $V_{CE} = 10 \text{ J}$ )  Toro-Off Time ( $V_{CE} = 10 \text{ J}$ )  Toro-Off Time ( $V_{CE} = 10 \text{ J}$ )  Toro-Off Time ( $V_{CE} = 10 \text{ J}$ )  Toro-Off Time ( $V_{CE} = 10 \text{ J}$ )  Toro-Off Time ( $V_{CE} = 10 \text{ J}$ )	30 70	0.2 100 45	500 20	μΑ
$(V_{CE} = 30 \text{ V, } T_{A} = 100^{\circ}\text{C})$ $Collector-Base Dark Current (V_{CB} = 10 \text{ V}) \qquad T_{A} = 25^{\circ}\text{C} \\ T_{A} = 100^{\circ}\text{C}$ $Collector-Emitter Breakdown Voltage (I_{C} = 1 \text{ mA}) \qquad V(BR)CEO$ $Collector-Base Breakdown Voltage (I_{C} = 100 \mu\text{A}) \qquad V(BR)CEO$ $Emitter-Base Breakdown Voltage (I_{E} = 100 \mu\text{A}) \qquad V(BR)CEO$ $DC Current Gain (I_{C} = 2 \text{ mA, } V_{CE} = 5 \text{ V}) \qquad h_{FE}$ $Collector-Emitter Capacitance (f = 1 \text{ MHz, } V_{CB} = 0) \qquad C_{CE}$ $Collector-Base Capacitance (f = 1 \text{ MHz, } V_{CB} = 0) \qquad C_{CB}$ $Emitter-Base Capacitance (f = 1 \text{ MHz, } V_{CB} = 0) \qquad C_{CB}$ $Emitter-Base Capacitance (f = 1 \text{ MHz, } V_{CB} = 0) \qquad C_{CB}$ $CoupleD$ $CoupleD$ $Couput Collector Current (I_{F} = 10 \text{ mA, } V_{CE} = 10 \text{ V}) \qquad T_{A} = -55^{\circ}\text{C} \qquad T_{A} = 100^{\circ}\text{C}$ $Collector-Emitter Saturation Voltage (I_{C} = 0.5 \text{ mA, } I_{F} = 10 \text{ mA}) \qquad V_{CE}(sat)$ $Turn-On Time \qquad ton \qquad t$	30 70	0.2 100 45	500 20	μΑ
$T_{A} = 100^{\circ}C$ Collector–Emitter Breakdown Voltage ( $I_{C} = 1 \text{ mA}$ ) $V(BR)CEO$ Collector–Base Breakdown Voltage ( $I_{C} = 100  \mu A$ ) $V(BR)CBO$ Emitter–Base Breakdown Voltage ( $I_{E} = 100  \mu A$ ) $V(BR)EBO$ DC Current Gain ( $I_{C} = 2 \text{ mA}, V_{CE} = 5 \text{ V}$ ) $Collector–Emitter Capacitance (f = 1 \text{ MHz}, V_{CE} = 0) CCE Collector–Base Capacitance (f = 1 \text{ MHz}, V_{CE} = 0) CCB Emitter–Base Capacitance (f = 1 \text{ MHz}, V_{CB} = 0) CEB COUPLED COUPLED Output Collector Current (I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}) I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}) I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V} I_{C} = 10 \text{ mA} I_{C} = 10 \text{ mA}$	70	100 45		nA
Collector–Base Breakdown Voltage ( $I_C = 100  \mu A$ )  Emitter–Base Breakdown Voltage ( $I_E = 100  \mu A$ )  DC Current Gain ( $I_C = 2  \text{mA}$ , $V_{CE} = 5  \text{V}$ )  Collector–Emitter Capacitance ( $f = 1  \text{MHz}$ , $V_{CE} = 0$ )  CCE  Collector–Base Capacitance ( $f = 1  \text{MHz}$ , $V_{CB} = 0$ )  Emitter–Base Capacitance ( $f = 1  \text{MHz}$ , $V_{CB} = 0$ )  CCB  COUPLED  Output Collector Current  ( $I_F = 10  \text{mA}$ , $V_{CE} = 10  \text{V}$ )  TA = 25°C TA = 100°C  Collector–Emitter Saturation Voltage ( $I_C = 0.5  \text{mA}$ , $I_F = 10  \text{mA}$ )  VCE(sat)  Turn–On Time  Turn–Off Time  ( $I_C = 2  \text{mA}$ , $V_{CC} = 10  \text{V}$ ,  Rise Time $(I_C = 2  \text{mA}$ , $V_{CC} = 10  \text{V}$ ,  RL = 100 $\Omega$ )(3)	70			
Emitter–Base Breakdown Voltage ( $I_E = 100  \mu A$ )  DC Current Gain ( $I_C = 2  mA$ , $V_{CE} = 5  V$ )  Collector–Emitter Capacitance ( $f = 1  MHz$ , $V_{CE} = 0$ )  CCB  Emitter–Base Capacitance ( $f = 1  MHz$ , $V_{CB} = 0$ )  CCB  Emitter–Base Capacitance ( $f = 1  MHz$ , $V_{CB} = 0$ )  CCB  COUPLED  Output Collector Current ( $I_F = 10  mA$ , $I_F = 10  mA$ )  Collector–Emitter Saturation Voltage ( $I_C = 0.5  mA$ , $I_F = 10  mA$ )  Turn–On Time ( $I_C = 2  mA$ , $I_C = 10  V$ , $I_C = 10 $	-	100	_	V
DC Current Gain ( $I_C = 2 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ )  Collector–Emitter Capacitance ( $f = 1 \text{ MHz}$ , $V_{CE} = 0$ )  Collector–Base Capacitance ( $f = 1 \text{ MHz}$ , $V_{CB} = 0$ )  Emitter–Base Capacitance ( $f = 1 \text{ MHz}$ , $V_{CB} = 0$ )  CoupleD  Output Collector Current  ( $I_F = 10 \text{ mA}$ , $V_{CE} = 10 \text{ V}$ )  To a collector–Emitter Saturation Voltage ( $I_C = 0.5 \text{ mA}$ , $I_F = 10 \text{ mA}$ )  Turn–On Time  Turn–On Time $I_C = 2 \text{ mA}$ , $V_{CC} = 10 \text{ V}$ , $I_C = 2 \text{ mA}$ , $V_{CC} = 10 \text{ V}$ , $I_C = 2 \text{ mA}$ , $V_{CC} = 10 \text{ V}$ , $I_C = 2 \text{ mA}$ , $I_C = 10 \text{ V}$ , $I_C = 10 \text$	7		_	V
	,	7.8	_	V
	_	400	_	_
Emitter–Base Capacitance (f = 1 MHz, VEB = 0)  CoupleD  Output Collector Current $T_A = 25^{\circ}C$ $T_A = -55^{\circ}C$ $T_A = 100^{\circ}C$ Collector–Emitter Saturation Voltage (I <sub>C</sub> = 0.5 mA, I <sub>F</sub> = 10 mA)  Turn–On Time $T_{C} = 10 \text{ V}$ $T_{C} =$	_	7	_	pF
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	_	19	_	pF
$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	_	9	_	pF
$(I_F = 10 \text{ mA}, V_{CE} = 10 \text{ V}) \\ T_A = -55^{\circ}C \\ T_A = 100^{\circ}C \\ \\ \hline Collector-Emitter Saturation Voltage (I_C = 0.5 \text{ mA}, I_F = 10 \text{ mA}) \\ \hline Turn-On Time \\ \hline Turn-Off Time \\ \hline Rise Time \\ (I_C = 2 \text{ mA}, V_{CC} = 10 \text{ V}, \\ \hline R_L = 100 \ \Omega)(3) \\ \hline t_r$		•		
	10 (100) 4 (40) 4 (40)	30 (300) — —	_ _ _	mA (%)
	_	0.14	0.3	V
Rise Time $R_L = 100 \Omega)^{(3)}$ $t_r$	_	7.5	10	μs
THE TIME	_	5.7	10	1
Fall Time tt	_	3.2	_	
T dil Tillo	_	4.7	_	
Isolation Voltage (f = 60 Hz, t = 1 sec)	7500	_	_	Vac(pk)
Isolation Current <sup>(4)</sup> $(V_{I-O} = 3550 \text{ Vpk})$ 4N35 $(V_{I-O} = 2500 \text{ Vpk})$ 4N36 $(V_{I-O} = 1500 \text{ Vpk})$ 4N37		— — 8	100 100 100	μА
Isolation Resistance (V = 500 V) <sup>(4)</sup>	_		_	Ω
Isolation Capacitance (V = 0 V, f = 1 MHz)(4)	_ _ 10 <sup>11</sup>	_		

- 1. Always design to the specified minimum/maximum electrical limits (where applicable).
- 2. Current Transfer Ratio (CTR) =  $I_C/I_F \times 100\%$ .
- 3. For test circuit setup and waveforms, refer to Figure 11.
- 4. For this test, Pins 1 and 2 are common, and Pins 4, 5 and 6 are common.

#### **TYPICAL CHARACTERISTICS**

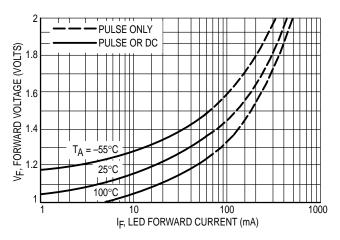


Figure 1. LED Forward Voltage versus Forward Current

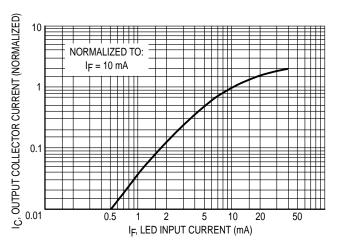


Figure 2. Output Current versus Input Current

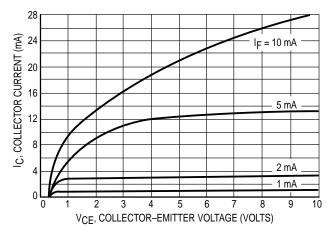


Figure 3. Collector Current versus Collector–Emitter Voltage

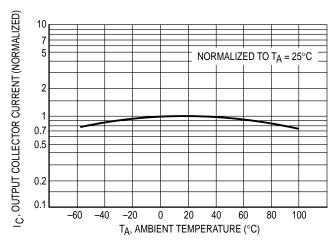


Figure 4. Output Current versus Ambient Temperature

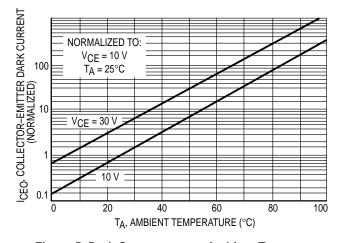


Figure 5. Dark Current versus Ambient Temperature

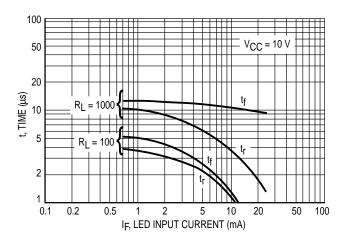


Figure 6. Rise and Fall Times (Typical Values)

### 4N35 4N36 4N37

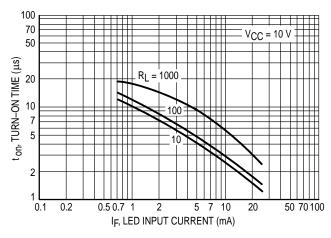


Figure 7. Turn-On Switching Times

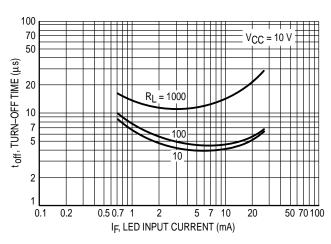


Figure 8. Turn-Off Switching Times

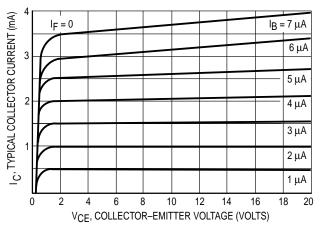


Figure 9. DC Current Gain (Detector Only)

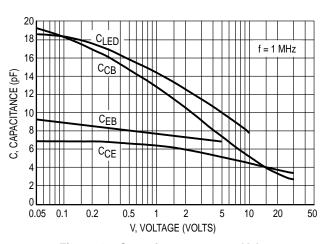


Figure 10. Capacitances versus Voltage

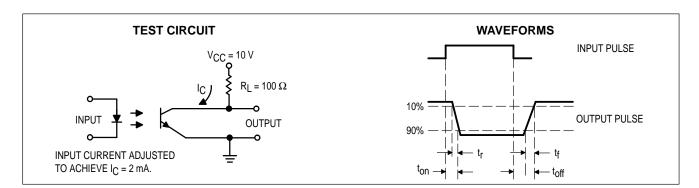
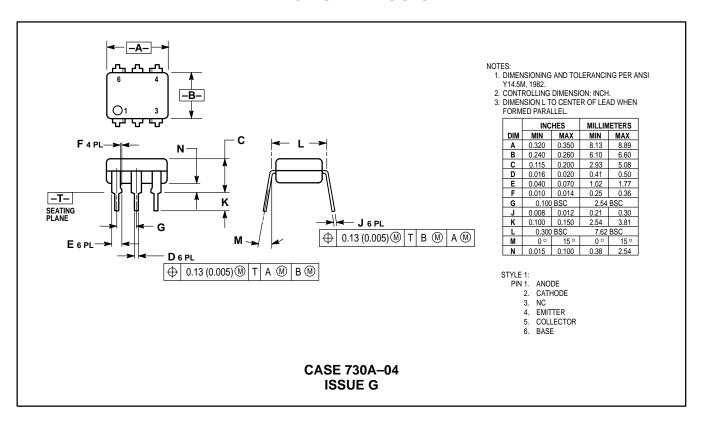
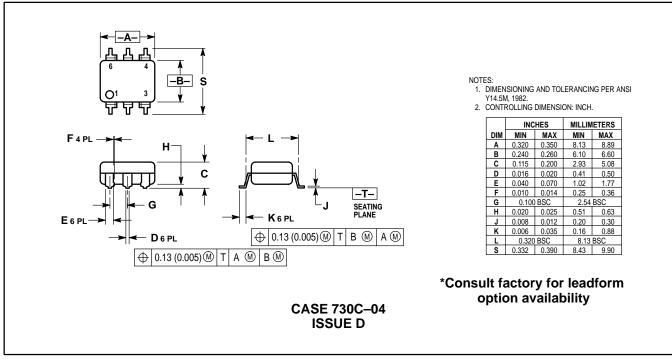


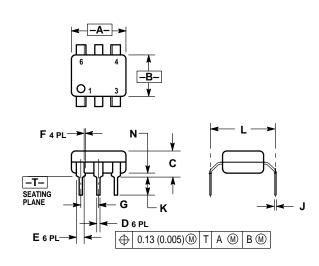
Figure 11. Switching Time Test Circuit and Waveforms

#### PACKAGE DIMENSIONS





#### 4N35 4N36 4N37



#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
   DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.

	INC	HES	MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.320	0.350	8.13	8.89	
В	0.240	0.260	6.10	6.60	
С	0.115	0.200	2.93	5.08	
D	0.016	0.020	0.41	0.50	
Е	0.040	0.070	1.02	1.77	
F	0.010	0.014	0.25	0.36	
G	0.100 BSC		2.54	BSC	
J	0.008	0.012	0.21	0.30	
K	0.100	0.150	2.54	3.81	
L	0.400	0.425	10.16	10.80	
N	0.015	0.040	0.38	1.02	

\*Consult factory for leadform option availability

CASE 730D-05 **ISSUE D** 

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